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**Practice for dosimetry in an electron
beam facility for radiation processing at
energies between 300 keV and 25 MeV**

*Pratique de la dosimétrie dans une installation de traitement par
irradiation utilisant un faisceau d'électrons d'énergies comprises
entre 300 keV et 25 MeV*



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Foreword

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ASTM International is one of the world's largest voluntary standards development organizations with global participation from affected stakeholders. ASTM technical committees follow rigorous due process balloting procedures.

A project between ISO and ASTM International has been formed to develop and maintain a group of ISO/ASTM radiation processing dosimetry standards. Under this project, ASTM Committee E61, Radiation Processing, is responsible for the development and maintenance of these dosimetry standards with unrestricted participation and input from appropriate ISO member bodies.

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International Standard ISO/ASTM 51649 was developed by ASTM Committee E61, Radiation Processing, through Subcommittee E61.03, Dosimetry Application, and by Technical Committee ISO/TC 85, Nuclear energy, nuclear technologies and radiological protection.

This third edition cancels and replaces the second edition (ISO/ASTM 51649:2005), which has been technically revised.

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